1. Scope :

This specification applies to PIN silicon photodiode chips,
Device No. PD-0394.

2. Structure :

2-1. Planar type : PIN diode.
2-2. Electrodes :
Top side (Anode & Cathode) : Aluminum alloy .
Back side (Cathode) : Gold alloy .

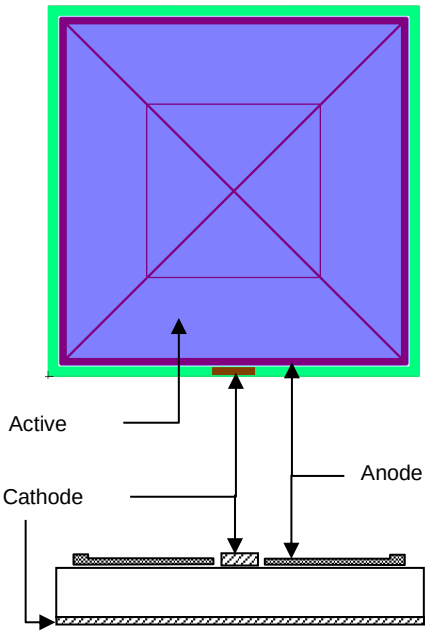
3. Size :

3-1. Chip size : 393.7 mils × 393.7 mils (10 mm × 10 mm) .
3-2. Chip thickness : 12 ± 1.5 mils (0.305 ± 0.038 mm).
3-3. Active area : 370 mils × 370 mils (9.4 mm × 9.4 mm).
3-4. Bonding pad : Anode 7.5 mils (0.190 mm) width of metal line.
Cathode : 7.87 mils × 45.7 mils (0.20 mm × 1.16 mm).
3-5. Pattern drawing : Refer to the attached drawing.

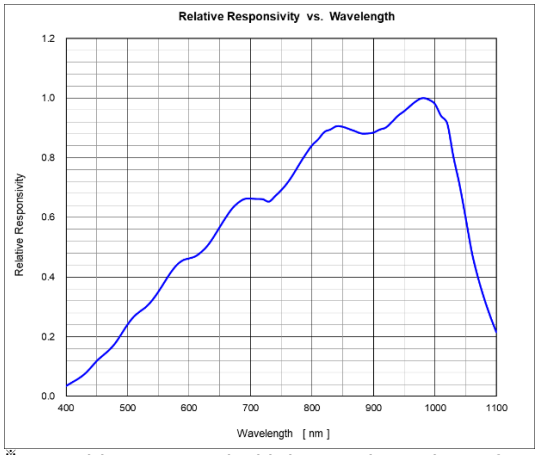
4. Electro-optical characteristics (Ta = 25℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
※Reverse dark current	I_D	V_R=5V Ee=0mW/cm^2			100	nA
Open circuit voltage	Voc	Ee=5mW/cm^2 T=2856K		450		mV
※Reverse breakdown voltage	$V_{(BR)R}$	I_R=100μA Ee=0mW/cm^2	10			V
Total Capacitance	C_T	V_R =0V Ee=0mW/cm^2 f=1MHz		700		pF
Short circuit Current	Isc	V_R =0V Ee=5mW/cm^2 T=2856K		750		μA

※Based on 100% probing



5. Relative spectral responsivity



※Bare chip measured with integrating sphere, for reference only.